

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
12V	4.8mΩ @ V <sub>GS</sub> = 4.5V	15A
	7.0mΩ @ V <sub>GS</sub> = 2.5V	12A

## Description

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

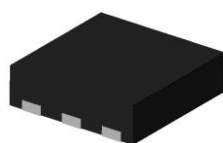
## Applications

- General Purpose Interfacing Switch
- Power Management Functions

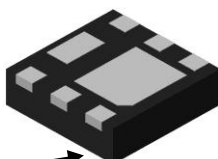
U-DFN2020-6 (Type F)



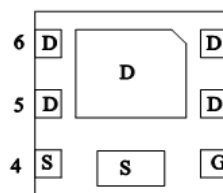
ESD PROTECTED



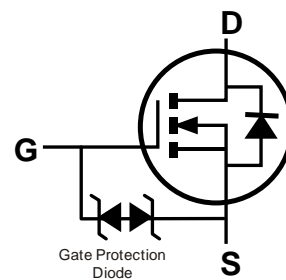
Top View



Bottom View



Pin Out  
Bottom View



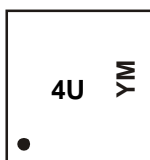
Equivalent Circuit

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN1004UFDF-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMN1004UFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



4U = Product Type Marking Code  
YM = Date Code Marking  
Y = Year (ex: E = 2017)  
M = Month (ex: 9 = September)

### Date Code Key

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	E	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	12	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	15 12	A
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	70	A
Maximum Body Diode Continuous Current (Note 6)			I <sub>S</sub>	3	A
Avalanche Current (Note 7) L = 0.1mH			I <sub>AS</sub>	34	A
Avalanche Energy (Note 7) L = 0.1mH			E <sub>AS</sub>	55	mJ

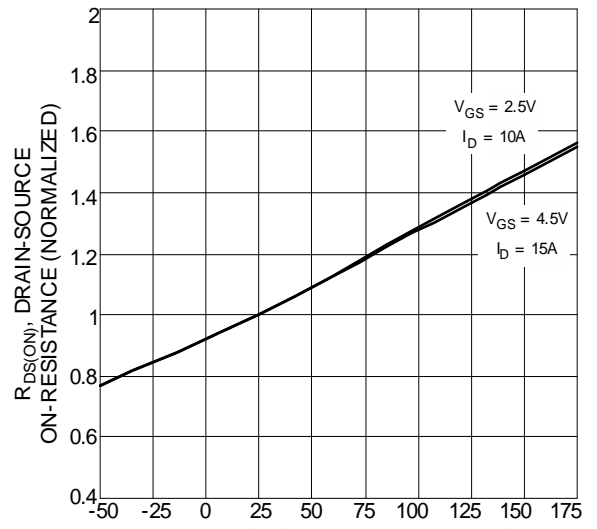
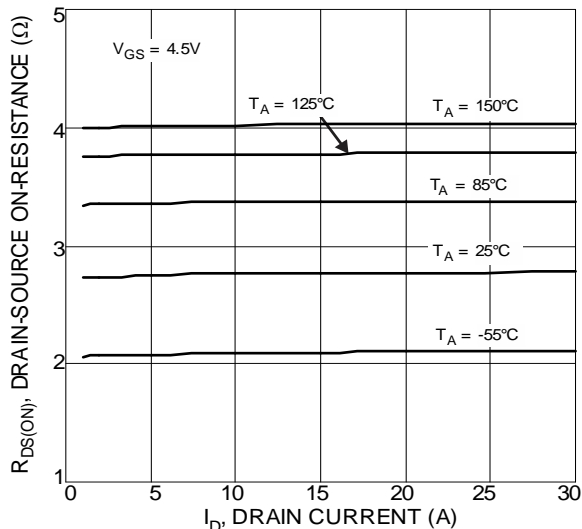
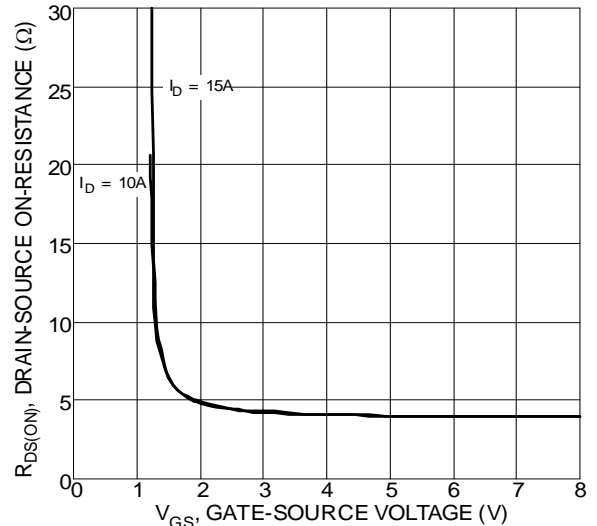
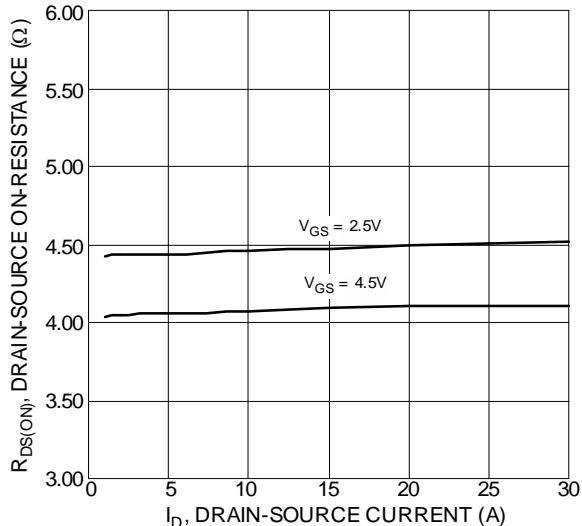
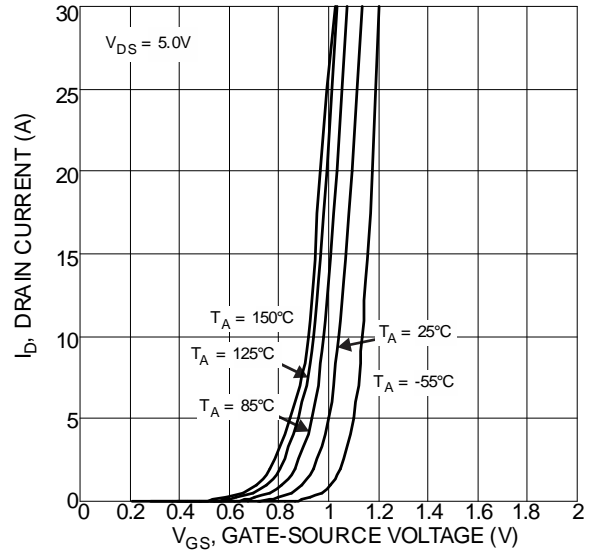
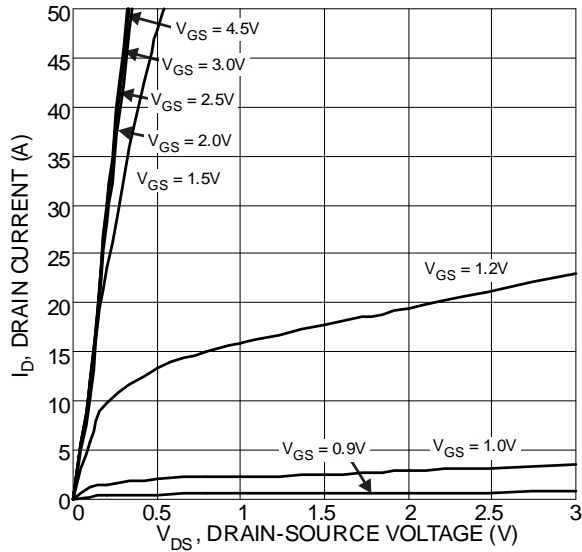
**Thermal Characteristics**

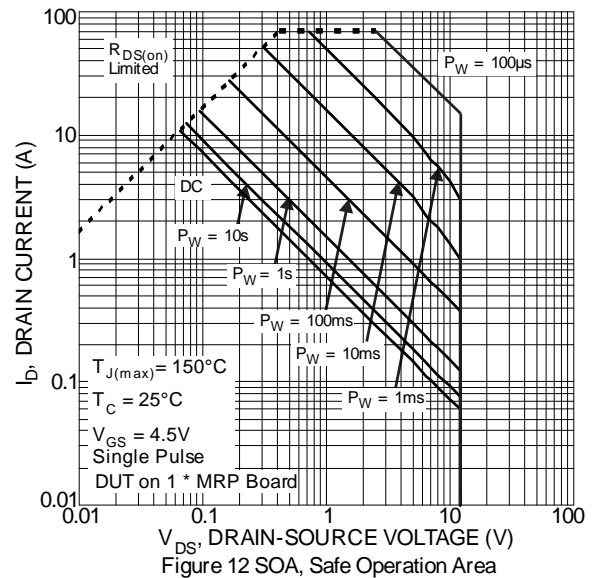
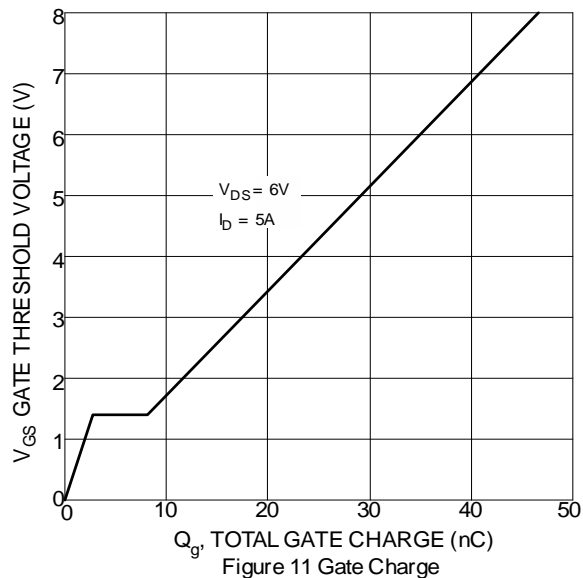
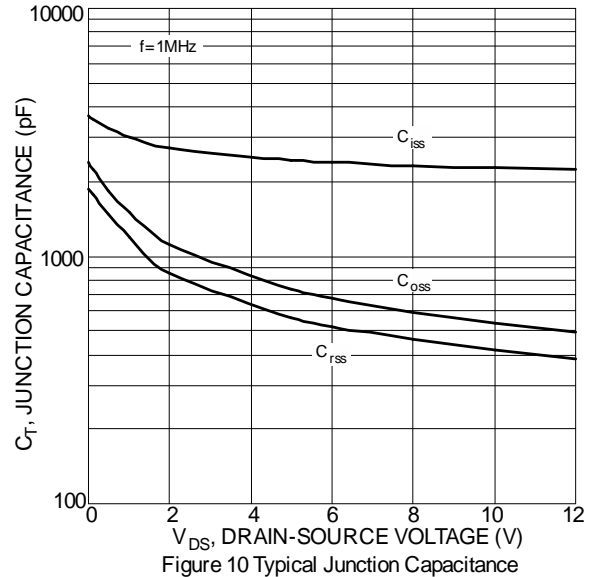
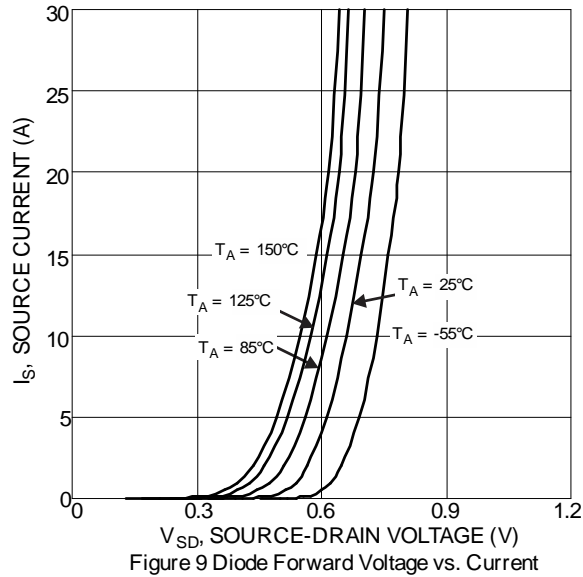
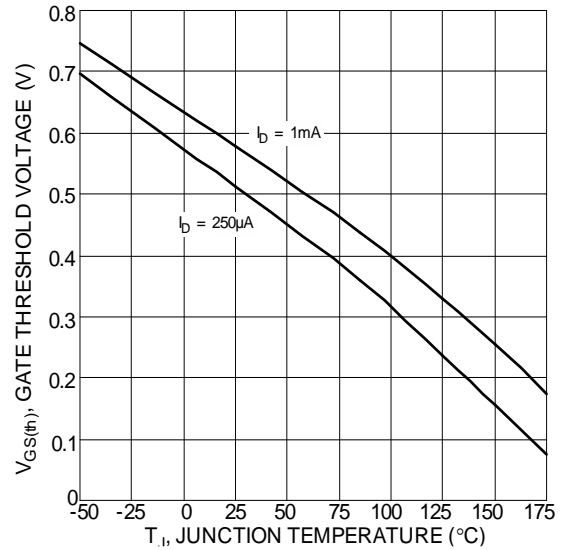
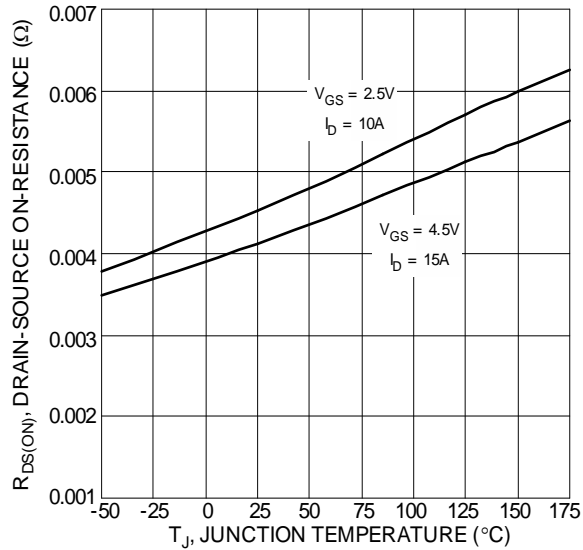
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	167	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	72	°C/W
Thermal Resistance, Junction to Case (Note 6)		R <sub>θJC</sub>	22	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

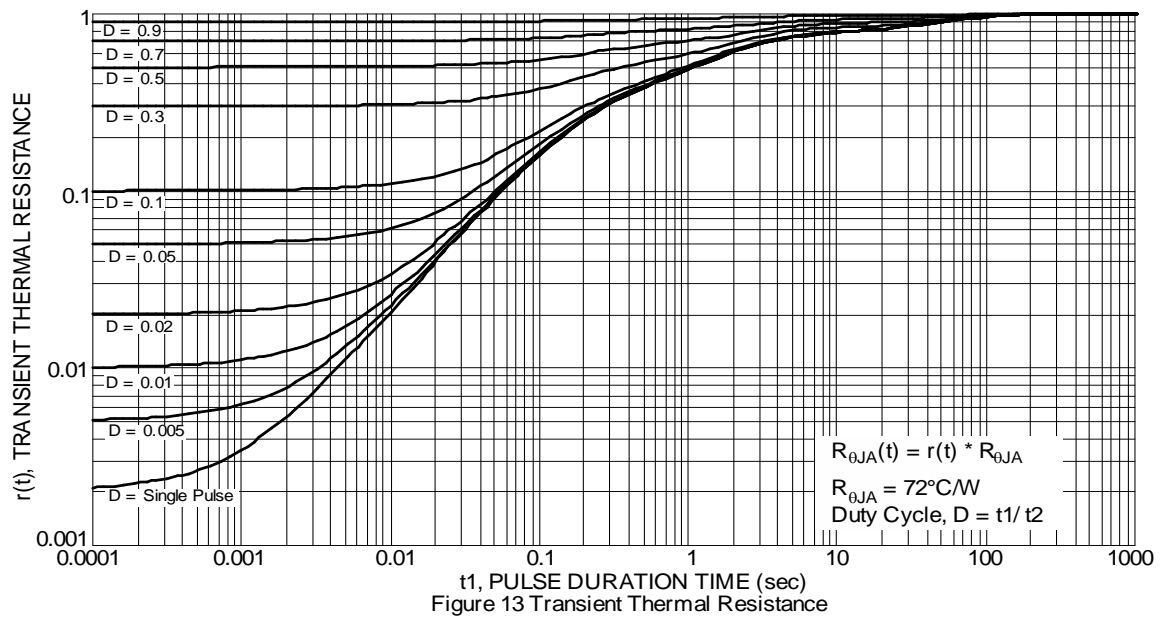
**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 8)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	12	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 9.6V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	µA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 8)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.3	—	1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	4.1	4.8	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 15A
		—	4.5	7.0		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 10A
Diode Forward Voltage	V <sub>SD</sub>	—	0.6	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 3.2A
<b>DYNAMIC CHARACTERISTICS</b> (Note 9)						
Input Capacitance	C <sub>ISS</sub>	—	2,385	—	pF	V <sub>DS</sub> = 6V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>OSS</sub>	—	678	—	pF	
Reverse Transfer Capacitance	C <sub>RSS</sub>	—	520	—	pF	
Gate Resistance	R <sub>G</sub>	—	2.2	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>G</sub>	—	26	—	nC	V <sub>DS</sub> = 6V, I <sub>D</sub> = 10A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>G</sub>	—	47	—	nC	
Gate-Source Charge	Q <sub>GS</sub>	—	2.8	—	nC	
Gate-Drain Charge	Q <sub>GD</sub>	—	5.3	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	5.3	—	ns	V <sub>DS</sub> = 6V, I <sub>D</sub> = 5.0A V <sub>GS</sub> = 4.5V, R <sub>G</sub> = 1.0Ω
Turn-On Rise Time	t <sub>R</sub>	—	10.7	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	31.6	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	16.9	—	ns	
Reverse Recovery Time	t <sub>RR</sub>	—	24.3	—	ns	I <sub>F</sub> = 2.0A, di/dt = 100A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	—	7.4	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
  - I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.



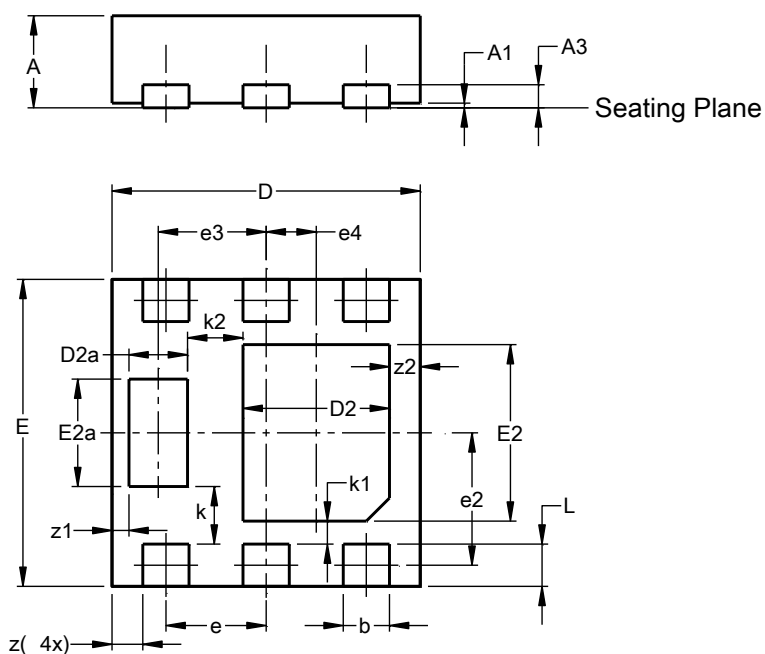




## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**U-DFN2020-6 (Type F)**

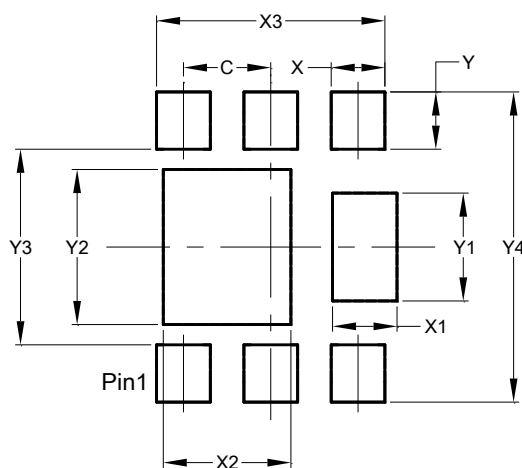


U-DFN2020-6 (Type F)			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0.00	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
D2a	0.33	0.43	0.38
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
E2a	0.65	0.75	0.70
e	0.65 BSC		
e2	0.863 BSC		
e3	0.70 BSC		
e4	0.325 BSC		
k	0.37 BSC		
k1	0.15 BSC		
k2	0.36 BSC		
L	0.225	0.325	0.275
z	0.20 BSC		
z1	0.110 BSC		
z2	0.20 BSC		
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**U-DFN2020-6 (Type F)**



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

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